

MOSFET – N-Channel, UniFET™, FRFET®

400 V, 23 A, 190 mΩ

FDA24N40F

Description

UniFET MOSFET is onsemi's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. The body diode's reverse recovery performance of UniFET FRFET MOSFET has been enhanced by lifetime control. Its trr is less than 100 ns and the reverse dv/dt immunity is 15 V/ns while normal planar MOSFETs have over 200 ns and 4.5 V/ns respectively. Therefore, it can remove additional component and improve system reliability in certain applications in which the performance of MOSFET's body diode is significant. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.

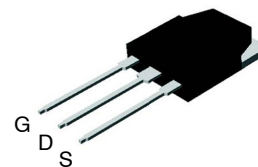
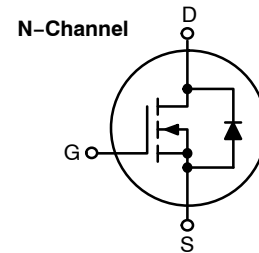
Features

- $R_{DS(on)} = 150 \text{ m}\Omega$ (Typ.) @ $V_{GS} = 10 \text{ V}$, $I_D = 11.5 \text{ A}$
- Low Gate Charge (Typ. 46 nC)
- Low C_{rss} (Typ. 25 pF)
- 100% Avalanche Tested
- RoHS Compliant

Applications

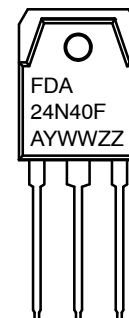
- Uninterruptible Power Supply
- AC-DC Power Supply

V_{DS}	$R_{DS(on)}$ MAX	I_D MAX
400 V	190 mΩ @ 10 V	23 A



TO-3P-3LD / EIAJ SC-65, ISOLATED
CASE 340BZ

MARKING DIAGRAM



FDA24N40F = Specific Device Code
A = Assembly Site
YWW = Date Code (Year & Work Week)
ZZ = Assembly Lot Number

ORDERING INFORMATION

Device	Package	Shipping
FDA24N40F	TO-3P-3LD	450 Units / Tube

FDA24N40F

MOSFET MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DSS}	Drain to Source Voltage		400	V
V_{GSS}	Gate to Source Voltage		± 30	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	23	A
		- Continuous ($T_C = 100^\circ\text{C}$)	13.8	
		- Pulsed (Note 1)	92	
I_{DM}				
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		1190	mJ
I_{AR}	Avalanche Current (Note 1)		23	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		23.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	235	W
		-Derate above $= 25^\circ\text{C}$	1.8	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. $L = 4.5\text{ mH}$, $I_{AS} = 23\text{ A}$, $V_{DD} = 50\text{ V}$, $R_G = 25\ \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 23\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.53	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV _{DSS}	Drain to Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0 V, T _J = 25°C	400	–	–	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, referenced to 25°C	–	0.5	–	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 400 V, V _{GS} = 0 V	–	–	10	μA
		V _{DS} = 320 V, T _C = 125°C	–	–	100	
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±30 V, V _{DS} = 0 V	–	–	±100	nA

ON CHARACTERISTICS

V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 250 μA	3.0	–	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 11.5 A	–	0.15	0.19	Ω
g _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 11.5 A	–	29	–	S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	–	2280	3030	pF
C _{oss}	Output Capacitance		–	370	490	pF
C _{rss}	Reverse Transfer Capacitance		–	25	38	pF
Q _{g(tot)}	Total Gate Charge at 10 V	V _{DS} = 320 V, I _D = 23 A, V _{GS} = 10 V (Note 4)	–	46	60	nC
Q _{gs}	Gate to Source Gate Charge		–	13	–	nC
Q _{gd}	Gate to Drain “Miller” Charge		–	18	–	nC

SWITCHING CHARACTERISTICS

t _{d(on)}	Turn-On Delay Time	V _{DS} = 200 V, I _D = 23 A, V _{GS} = 10 V, R _G = 25 Ω (Note 4)	–	40	90	ns
t _r	Turn-On Rise Time		–	92	195	ns
t _{d(off)}	Turn-Off Delay Time		–	120	250	ns
t _f	Turn-Off Fall Time		–	75	160	ns

DRAIN-SOURCE DIODE CHARACTERISTICS

I _S	Maximum Continuous Drain to Source Diode Forward Current		–	–	23	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		–	–	92	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 23 A	–	–	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 23 A, dI _F /dt = 100 A/μs	–	110	–	ns
Q _{rr}	Reverse Recovery Charge		–	0.3	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS

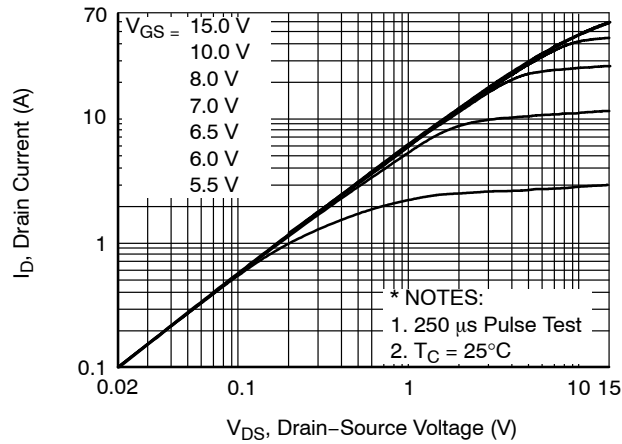


Figure 1. On-Region Characteristics

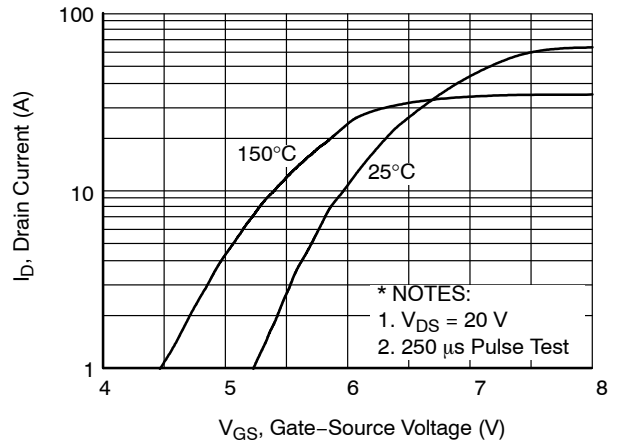


Figure 2. Transfer Characteristics

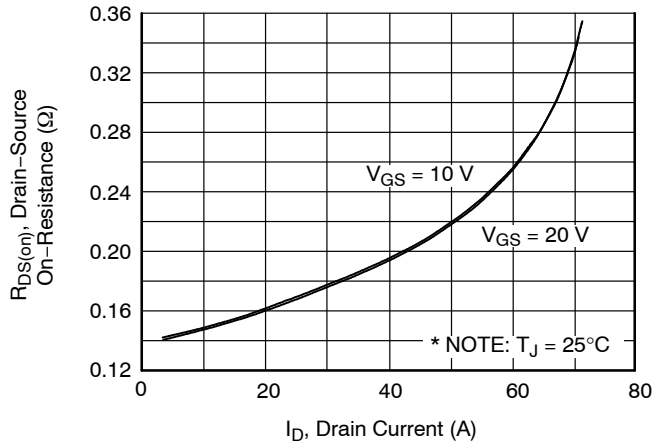


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

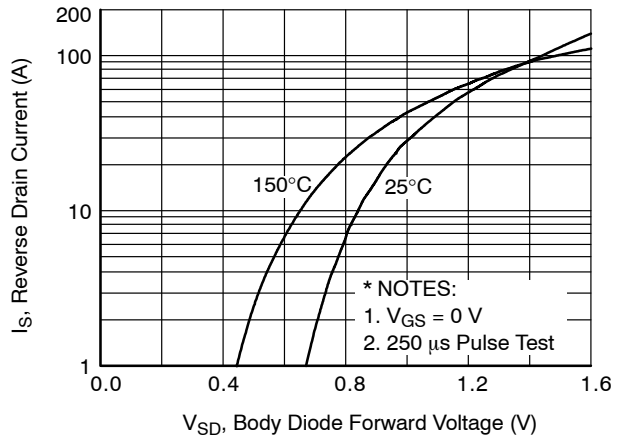


Figure 4. Body Diode Forward Voltage Variation vs. Source Current And Temperature

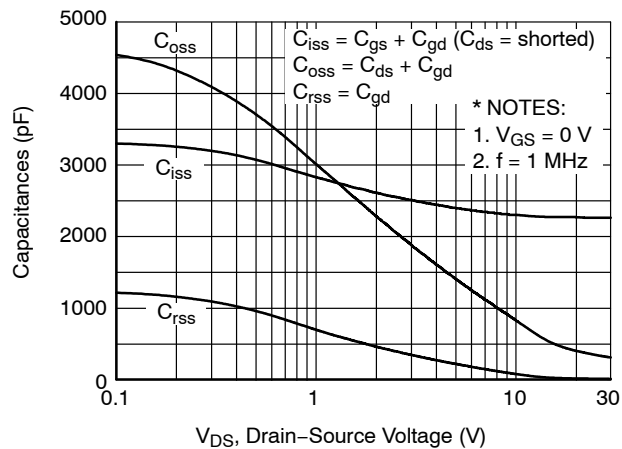


Figure 5. Capacitance Characteristics

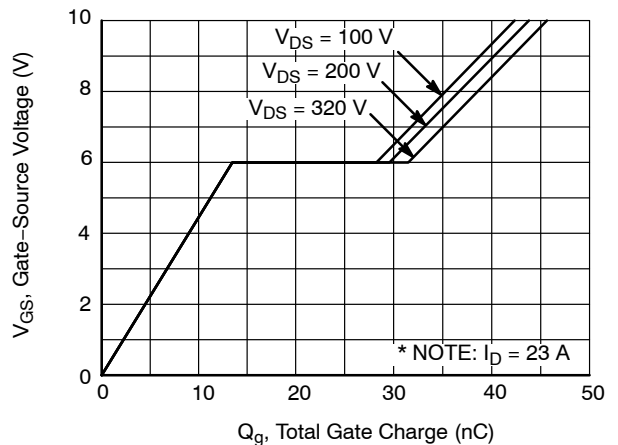


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

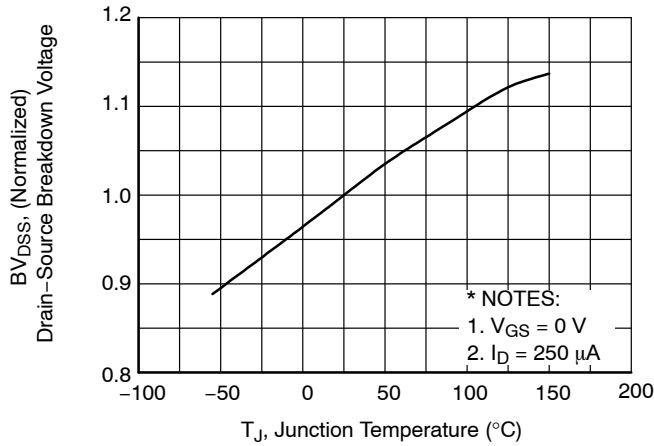


Figure 7. Breakdown Voltage Variation vs. Temperature

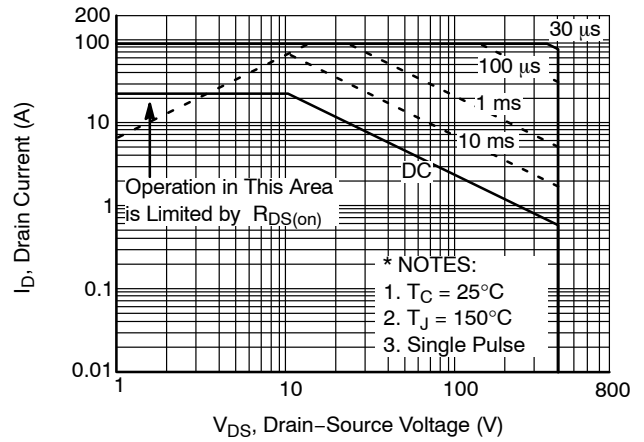


Figure 8. Maximum Safe Operating Area

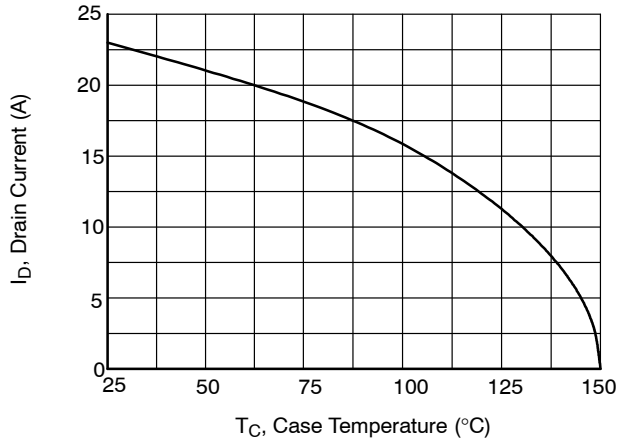


Figure 9. Maximum Drain Current vs. Case Temperature

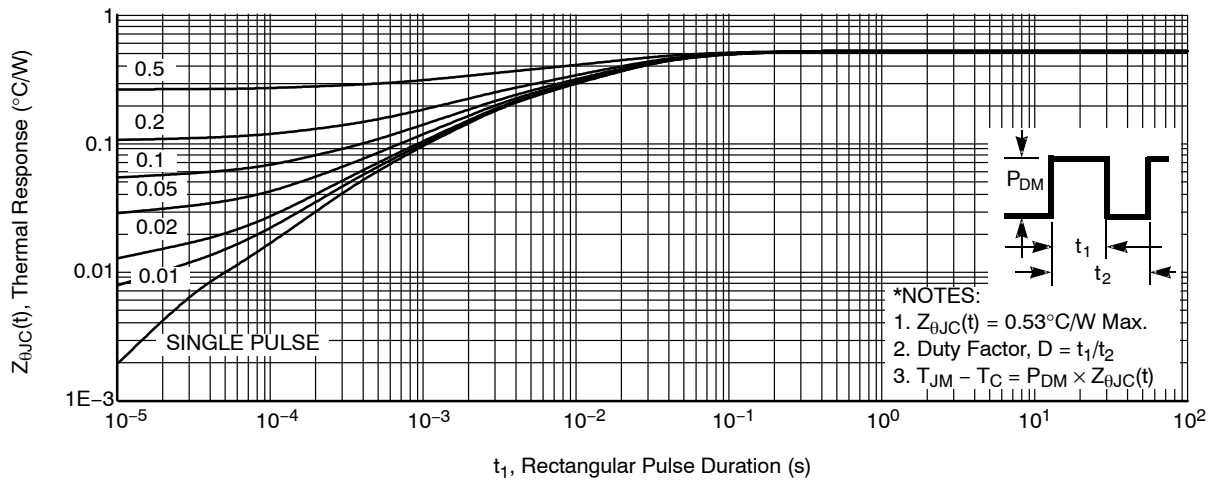


Figure 10. Transient Thermal Response Curve

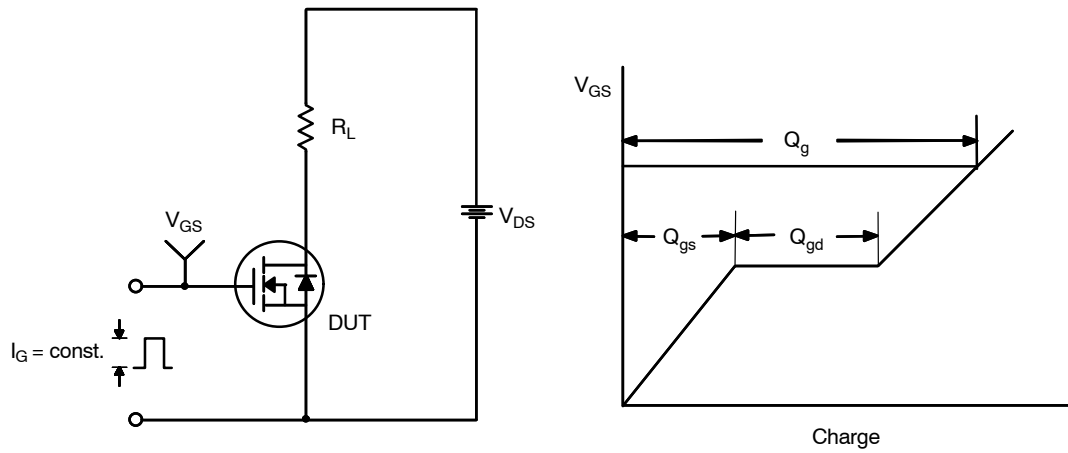


Figure 11. Gate Charge Test Circuit & Waveform

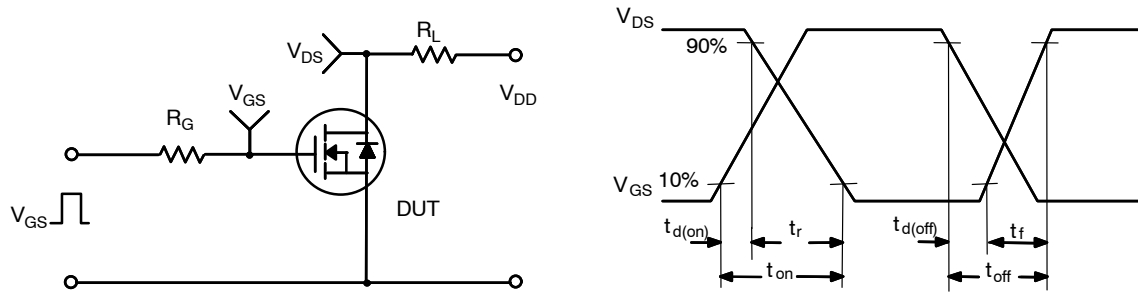


Figure 12. Resistive Switching Test Circuit & Waveforms

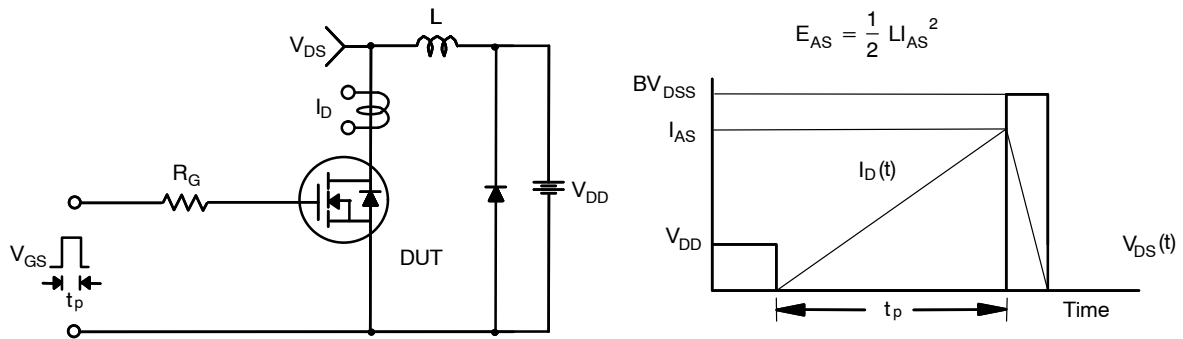


Figure 13. Unclamped Inductive Switching Test Circuit & Waveforms

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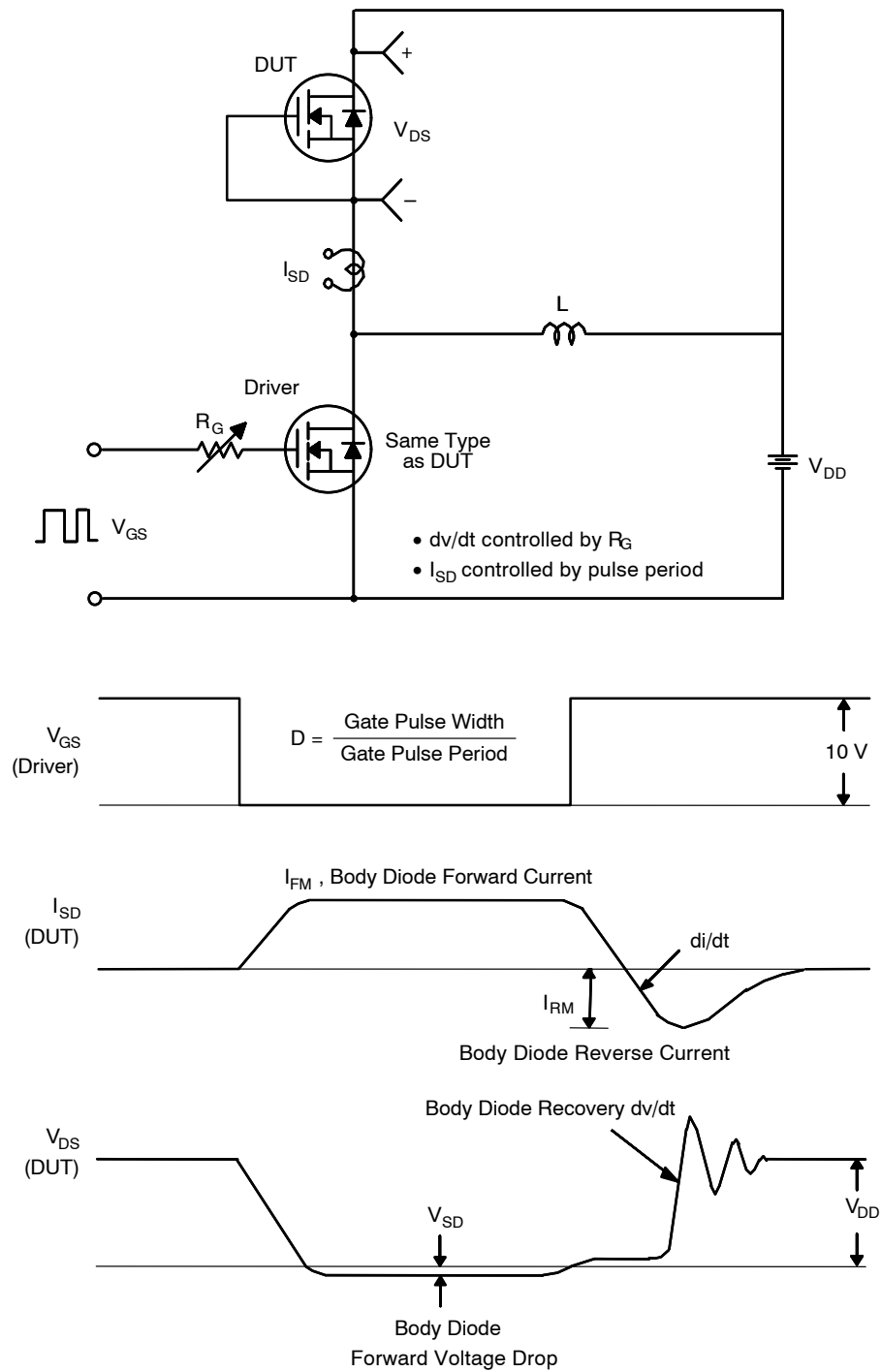


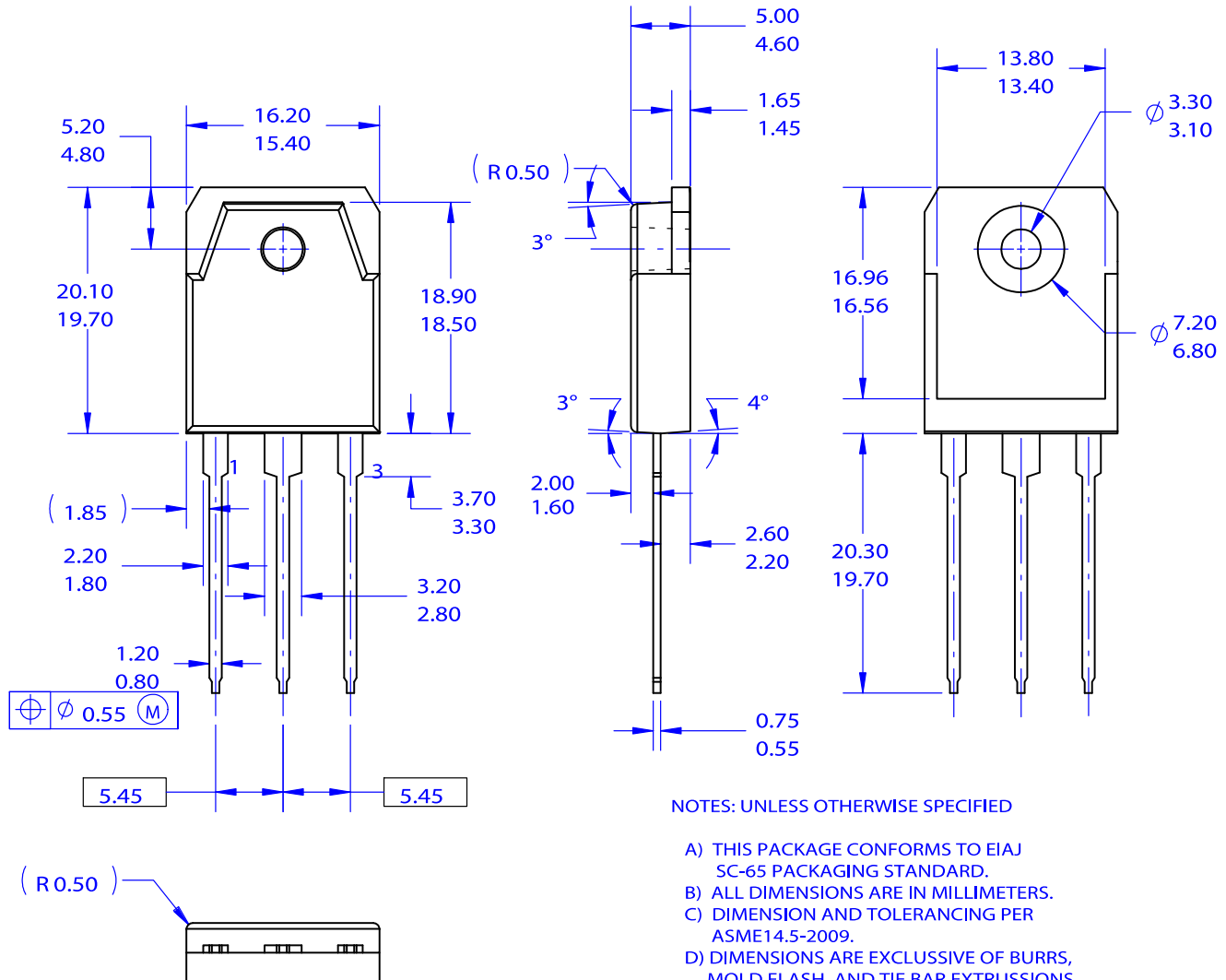
Figure 14. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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CASE 340BZ
ISSUE O

DATE 31 OCT 2016



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